TOSHIBA Intelligent Power Device Silicon Monolithic Power MOS IC

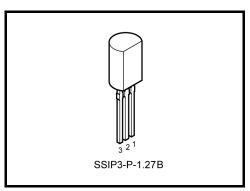
TPD1039S

Low-Side Switch for Motor, Solenoid and Lamp Drive

TPD1039S is a monolithic power IC for low-side switch. The IC has a vertical MOSFET output which can be directly driven from a CMOS or TTL logic circuit (e.g., an MPU). The IC offers intelligent self-protection functions.

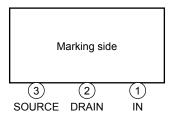
Features

- A monolithic power IC with a new structure combining a control block and a vertical power MOSFET (π -MOS) on a single chip.
- Can directly drive a power load from a CMOS or TTL logic.
- Built-in protection circuits against overvoltage, overheat, and overcurrent.
- Low ON-resistance: RDS (ON) = 0.25 Ω (max) (@VIN = 5 V, T_{ch} = 25°C)
- Package TO-92 (MOD) can be packed in tape.

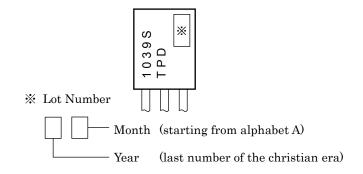


Weight: 0.36 g (typ.)

Pin Assignment



Marking

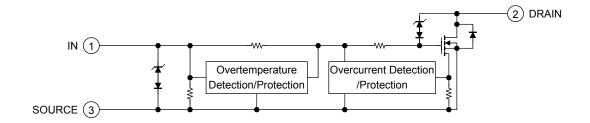


That because of its MOS structure, this product is sensitive to static electricity.

TPD1039S



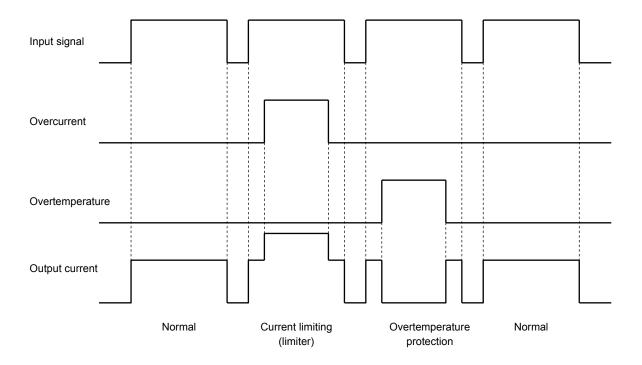
Block Diagram



Pin Description

Pin No.	Symbol	Pin Description			
1	IN	Input pin. This pin is connected to a pull-down resistor internally, so that even when input wiring is open-circuited, output can never be turned on inadvertently.			
2	DRAIN	Output pin. The current limit for output current is 5 A (typ.) when excessive current flow into a device because of in-rush current and short load of a lamp.			
3	SOURCE	Ground pin.			

Timing Chart



2

Truth Table

V _{IN}	V _{DRAIN}	State		
L	Н	Normal		
Н	L	Normal		
L	Н	Overcurrent		
Н	L	Overcurrent		
L	Н	Overtemperature		
Н	Н	Overtemperature		

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V _{DS (DC)}	45	V
Drain current	I _{D (DC)}	1.5	Α
Input voltage	V_{IN}	-0.5~6	V
Power dissipation (Ta = 25°C)	P_{D}	0.9	W
Single pulse active clamp capability (Note 1)	E _{AS}	20	mJ
Active clamp current	I _{AR}	1.5	Α
Repetitive active clamp capability (Note 2)	E _{AR}	0.09	mJ
Operating temperature	T _{opr}	−40~85	°C
Channel temperature	T _{ch}	150 (Note 3)	°C
Storage temperature range	T _{stg}	-55~150	°C

Note 1: Active clamp capability (single pulse) test condition $V_{DD}=25~V,~Starting~T_{ch}=25^{\circ}C,~L=10~mH,~I_{AR}=1.5~A,~R_{G}=25~\Omega$

Note 2: Repetitive rating; pulse width limited by maximum channel temperature.

Note 3: Overtemperature protection will work when the channel temperature exceeds 125°C.

Be sure to operate the device in such a way that the channel temperature does not exceed 125°C.

Note4: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

3

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch-a)}	139	°C/W

Electrical Characteristics (Tch = 25°C)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Drain-source clamp voltage	V _{(CL) DSS}	_	$V_{IN} = 0 \text{ V}, I_D = 1 \text{ mA}$	45	_	_	V
High level input voltage	V _{IH}	_	V _{DS} = 10~40 V, I _D ≥ 1 A	3.5	_	6	V
Low level input voltage	V_{IL}	_	$V_{DS} = 10~40 \text{ V}, I_{D} \le 10 \mu\text{A}$	_	_	0.8	V
Draint cut-off current	I _{DSS}	_	$V_{IN} = 0 \text{ V}, V_{DS} = 40 \text{ V}$	_	_	10	μА
Input current	I _{IN}	_	V _{IN} = 5 V, at normal operation	_	_	400	μΑ
Drain-source on resistance	R _{DS} (ON)	_	V _{IN} = 5 V, I _D = 1 A	_	_	0.25	Ω
Thermal shutdown (Note 4)	T _S	_	V _{IN} = 5 V	125	_	_	°C
Overcurrent protection	IS	_	V _{IN} = 5 V	_	5	_	Α
Switching time	toN	1	$\begin{aligned} &V_{DD}=24 \text{ V, } V_{IN}=5 \text{ V,} \\ &R_L=24 \Omega \end{aligned}$	_	15	_	μS
Switching time	t _{OFF}			_	45	_	
Source-drain diode forward voltage	V _{DSF}		I _F = 1.5 A		0.9	1.8	٧

Note 4: Overtemperature protection will work when the channel temperature exceeds 125°C.

Be sure to operate the device in such a way that the channel temperature does not exceed 125°C.

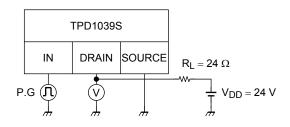
The overtemperature protection function protects a device from destruction.

Once started, however, this function will operate continuously; device reliability is not guaranteed while the function is in operation.

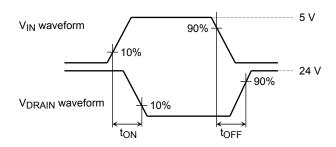
Test Circuit 1

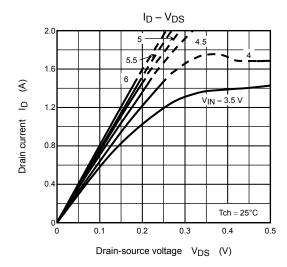
Switching time measuring circuit

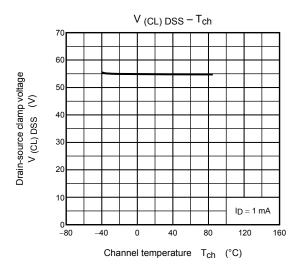
Test circuit

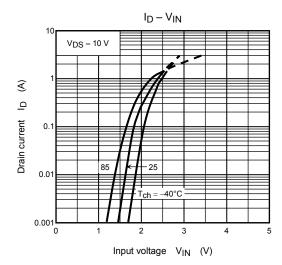


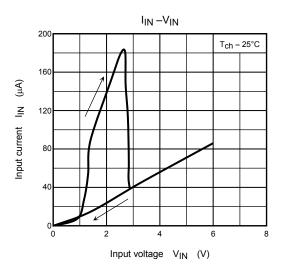
Measured waveforms

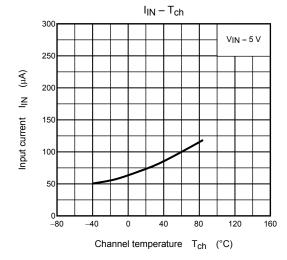


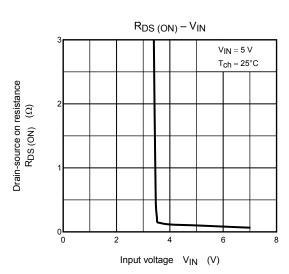




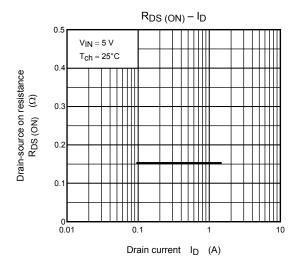


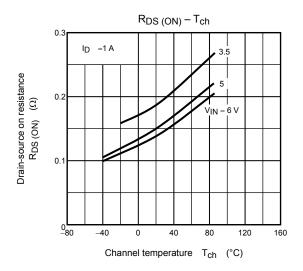


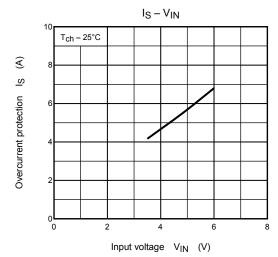


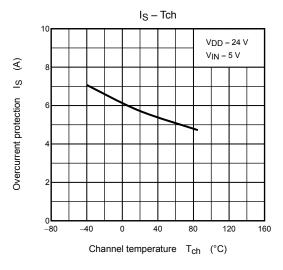


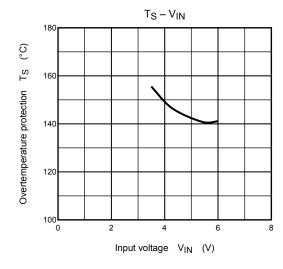
5

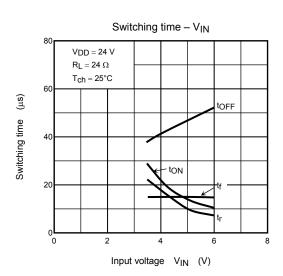


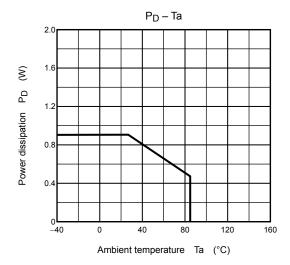


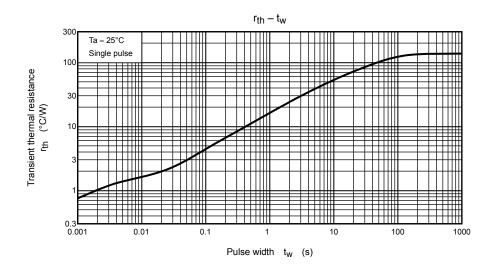








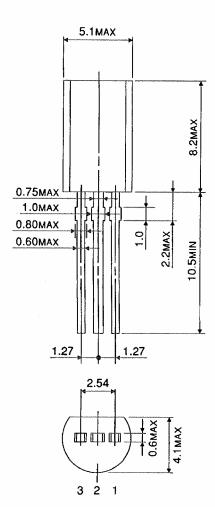




Unit: mm

Package Dimensions

SSIP3-P-1.27B



Weight: 0.36 g (typ.)

8 2006-10-31

RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
 compatibility. Please use these products in this document in compliance with all applicable laws and regulations
 that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
 occurring as a result of noncompliance with applicable laws and regulations.

9